

FORM PTO-1449	Atty. Docket No.: B784.312-0001	Application No.: 10/017,734
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	First Named Inventor: Baowei KANG et al.	
	Filing Date: December 7, 2001	Group Art: 2826 2823

U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Date	Name	Class	Sub Class	Filing Date If Appropriate
AA						
AB						
AC						
AD						
AE						
AF						

FOREIGN PATENT DOCUMENTS

	Document No.	Date	Country	Class	Sub Class	Translation Yes No
AG						
AH						
AI						

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

<u>K.N.</u>	AJ	Hideo Iwamoto et al., "A New Punch-Through IGBT Having a New n-Buffer Layer", IEEE TRANSACTIONS ON INDUSTRY APPLICATIONS, Vol. 38, No. 1, January/February 2002, pp. 168-174.
<u>K.N.</u>	AK	T. Laska et al., "Optimizing the Vertical IGBT Structure - The NPT Concept as the Most Economic and Electrically Ideal Solution for a 1200V-IGBT", Proceedings of the ISPSD 1996, pp. 169-172.
<u>K.N.</u>	AL	Darryl Burns et al., "NPT-IGBT - Optimizing for Manufacturability", Proceedings of the ISPSD 1996, pp. 331-334.]
<u>K.N.</u>	AM	K. Mochizuki et al., "Examination of Punch Through IGBT(PT-IGBT) for High Voltage and High Current Applications", PROCEEDINGS of the ISPSD 1997, pp. 237-240.
<u>K.N.</u>	AN	G. Miller et al., "A New Concept for a Non Punch Through IGBT with MOSFET Like Switching Characteristics", 20th Annual IEEE Power Electronics Specialists Conference, 1989, pp. 21-25.
<u>K.N.</u>	AO	B. J. Baliga et al., "The Insulated Gate Rectifier (IGR): A New Power Switching Device", IEDM Technical Digest, 1982, pp. 264-267.

EXAMINER: Shienguyen DATE CONSIDERED: 03/22/03

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.